CSD18532KCS 60V N-Channel NexFET™ Power MOSFET

1 Features

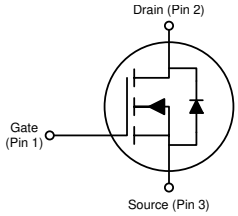
- Ultra-low Q_g and Q_{gd}
- Low thermal resistance
- Avalanche rated
- Logic level
- Pb free terminal plating
- RoHS compliant
- Halogen free
- TO-220 plastic package

2 Applications

- DC-DC conversion
- Secondary side synchronous rectifier
- Motor control

Description

This 60V, 3.3mΩ, TO-220 NexFET™ power MOSFET is designed to minimize losses in power conversion applications.





Product Summary

T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	60		V
Q_g	Gate Charge Total (10V)	44		nC
Q_{gd}	Gate Charge Gate-to-Drain	6.9		nC
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = 4.5V	4.2	mΩ
		V_{GS} = 10V	3.3	mΩ
$V_{GS(th)}$	Threshold Voltage	1.8		V

Ordering Information(1)

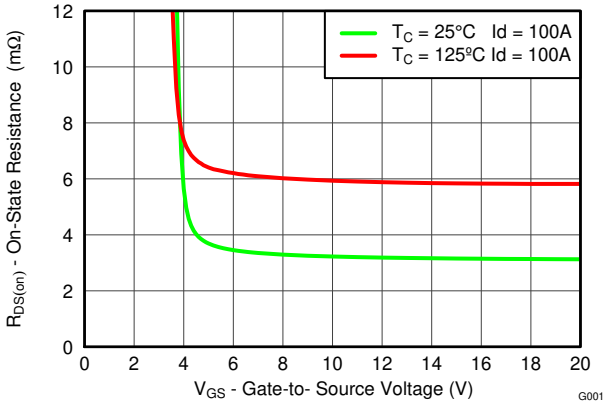
Device	Package	Media	Qty	Ship
CSD18532KCS	TO-220 Plastic Package	Tube	50	Tube

(1) For all available packages, see the orderable addendum at the end of the data sheet.

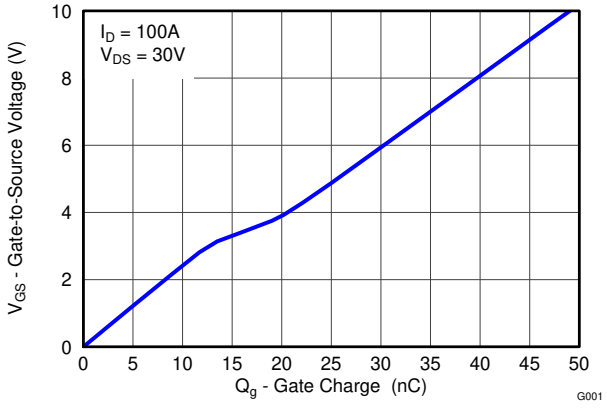
Absolute Maximum Ratings

T_A = 25°C		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current (Package limited), T_C = 25°C	100	A
	Continuous Drain Current (Silicon limited), T_C = 25°C	169	
	Continuous Drain Current (Silicon limited), T_C = 100°C	116	
I_{DM}	Pulsed Drain Current (1)	400	A
P_D	Power Dissipation	250	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	–55 to 175	°C
E_{AS}	Avalanche Energy, single pulse I_D = 75A, L = 0.1mH, R_G = 25Ω	281	mJ

(1) Pulse duration ≤300µs, duty cycle ≤2%



$R_{DS(on)}$ vs V_{GS}



Gate Charge

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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3 Specifications

3.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0V, I_D = 250µA	60			V
I_{DSS}	Drain-to-Source Leakage Current	V_{GS} = 0V, V_{DS} = 48V			1	µA
I_{GSS}	Gate-to-Source Leakage Current	V_{DS} = 0V, V_{GS} = 20V			100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	1.5	1.8	2.2	V
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = 4.5V, I_D = 100A		4.2	5.3	mΩ
		V_{GS} = 10V, I_D = 100A		3.3	4.2	mΩ
g_{fs}	Transconductance	V_{DS} = 30V, I_D = 100A		187		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 30V, f = 1MHz		3900	4680	pF
C_{oss}	Output Capacitance			470	564	pF
C_{rss}	Reverse Transfer Capacitance			11	14	pF
R_G	Series Gate Resistance			1.3	2.6	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 30V, I_D = 100A		21	25	nC
Q_g	Gate Charge Total (10V)			44	53	nC
Q_{gd}	Gate Charge Gate-to-Drain			6.9		nC
Q_{gs}	Gate Charge Gate-to-Source			10		nC
$Q_{g(th)}$	Gate Charge at V_{th}			7.3		nC
Q_{oss}	Output Charge	V_{DS} = 30V, V_{GS} = 0V		52		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 30V, V_{GS} = 10V, I_{DS} = 100A, R_G = 0Ω		7.8		ns
t_r	Rise Time			5.3		ns
$t_{d(off)}$	Turn Off Delay Time			24.2		ns
t_f	Fall Time			5.6		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	I_{SD} = 100A, V_{GS} = 0V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DS}= 30V, I_F = 100A, di/dt = 300A/µs		127		nC
t_{rr}	Reverse Recovery Time			57		ns

3.2 Thermal Information

(T_A = 25°C unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			0.6	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			62	

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3.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)

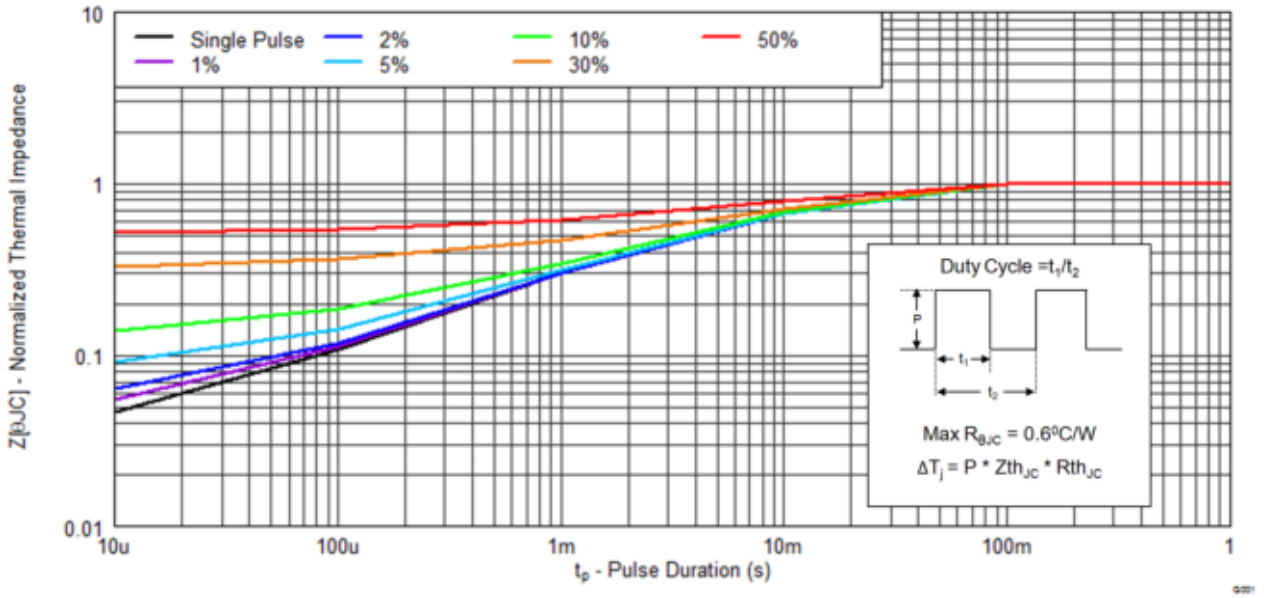

Figure 3-1. Transient Thermal Impedance

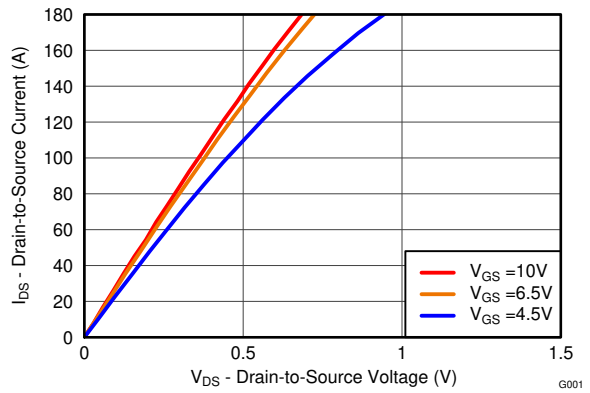

Figure 3-2. Saturation Characteristics

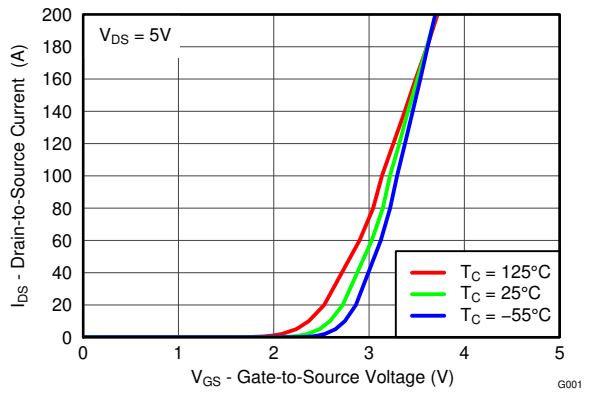

Figure 3-3. Transfer Characteristics

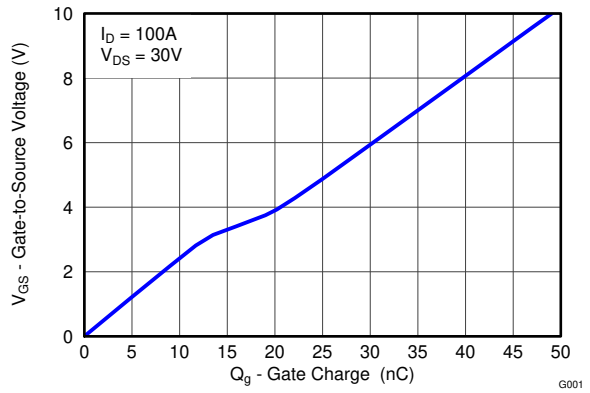

Figure 3-4. Gate Charge

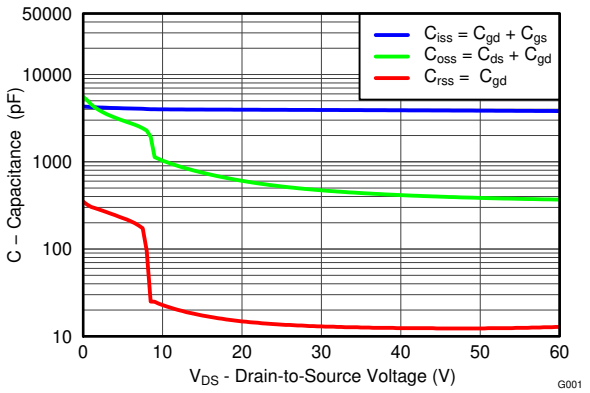

Figure 3-5. Capacitance

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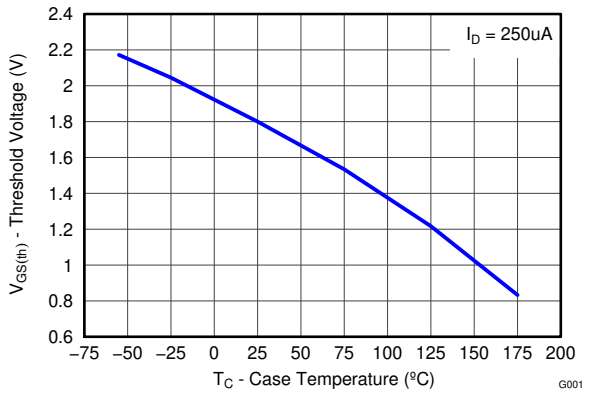

Figure 3-6. Threshold Voltage vs Temperature

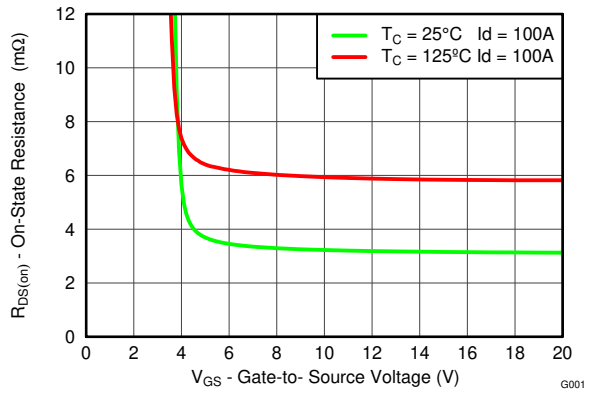

Figure 3-7. On-State Resistance vs Gate-to-Source Voltage

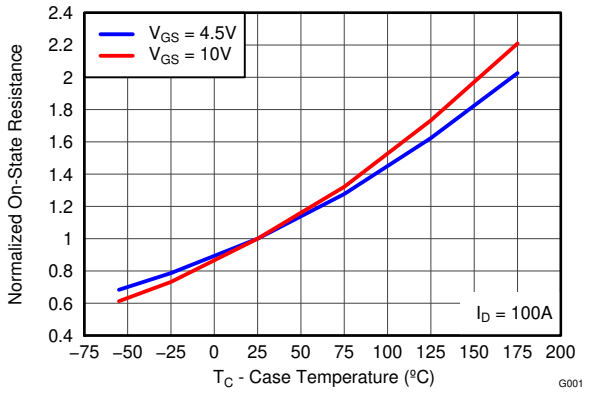

Figure 3-8. Normalized On-State Resistance vs Temperature

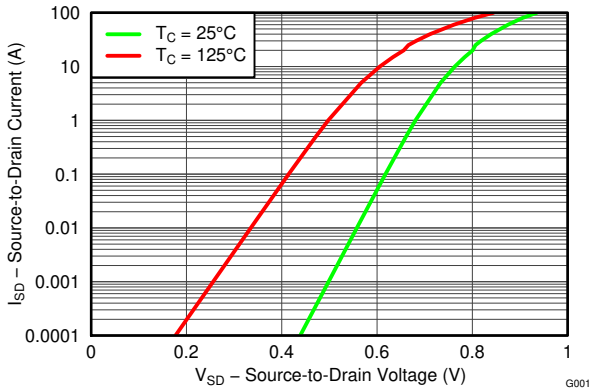

Figure 3-9. Typical Diode Forward Voltage

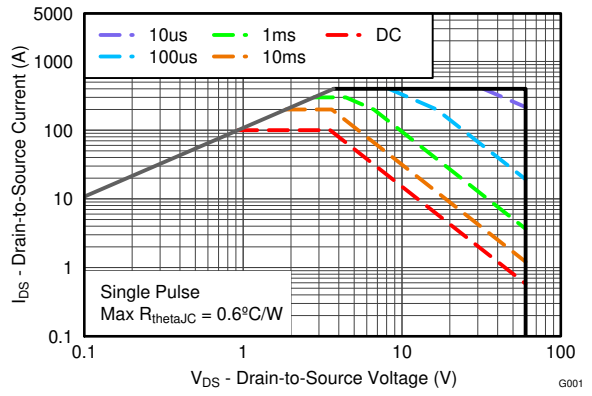

Figure 3-10. Maximum Safe Operating Area

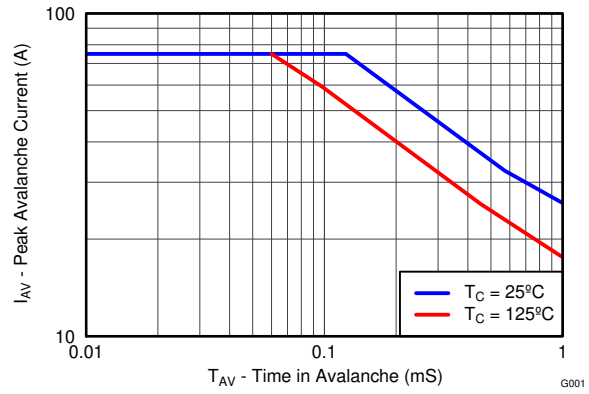

Figure 3-11. Single Pulse Unclamped Inductive Switching

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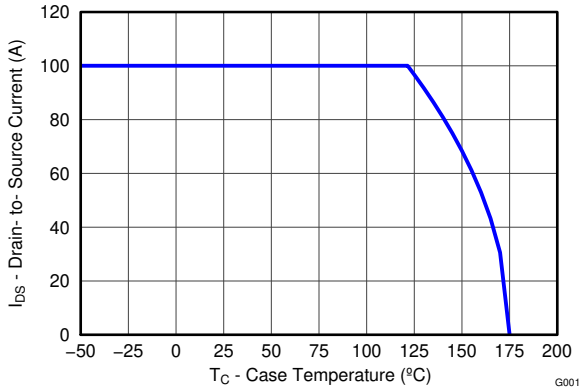

Figure 3-12. Maximum Drain Current vs Temperature

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4 Device and Documentation Support

4.1 Third-Party Products Disclaimer

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To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

4.3 Support Resources

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4.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

4.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

5 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (August 2012) to Revision C (March 2024)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document	1

Changes from Revision A (October 2012) to Revision B (July 2014)	Page
• Increased I_D at T_C = 100°C to 116A	1
• Increased I_{DM} to 400A	1
• Increased max operating junction and storage temperature to 175°C	1
• Updated Figure 3-1 from a normalized $R_{\theta JA}$ to an $R_{\theta JC}$ curve	4
• Updated Figure 3-6 to extend to 175°C	4
• Updated Figure 3-8 to extend to 175°C	4
• Updated the SOA in Figure 3-10	4
• Updated Figure 3-12 to extend to 175°C	4

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Changes from Revision * (August 2012) to Revision A (October 2012)	Page
• Changed the Transconductance TYP value From: 146S To: 187S	3
• Changed $R_{\theta JA}$ From: MAX = 62°C/W To: MAX = 65°C/W	3
• Changed Figure 3-2	4

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6 Mechanical Data

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD18532KCS	Active	Production	TO-220 (KCS) | 3	50 | TUBE	ROHS Exempt	SN	N/A for Pkg Type	-55 to 175	CSD18532KCS
CSD18532KCS.B	Active	Production	TO-220 (KCS) | 3	50 | TUBE	ROHS Exempt	SN	N/A for Pkg Type	-55 to 175	CSD18532KCS

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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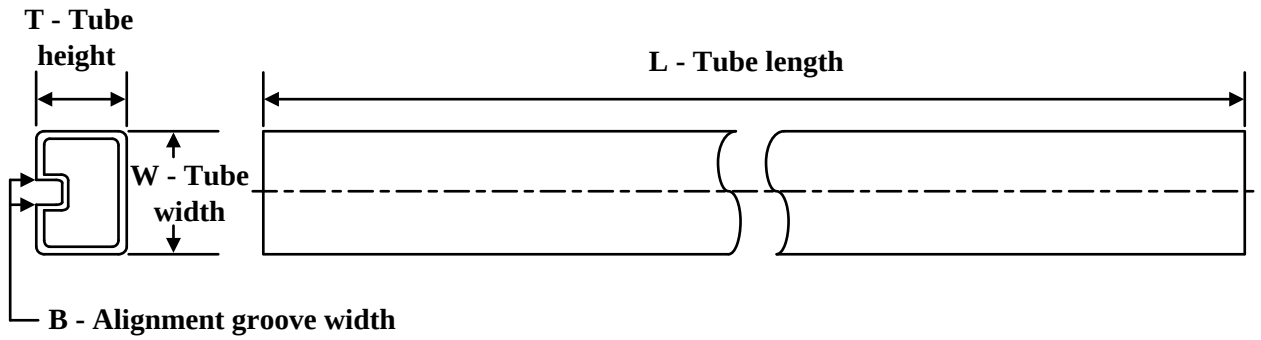
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CSD18532KCS	KCS	TO-220	3	50	532	34.1	700	9.6
CSD18532KCS.B	KCS	TO-220	3	50	532	34.1	700	9.6

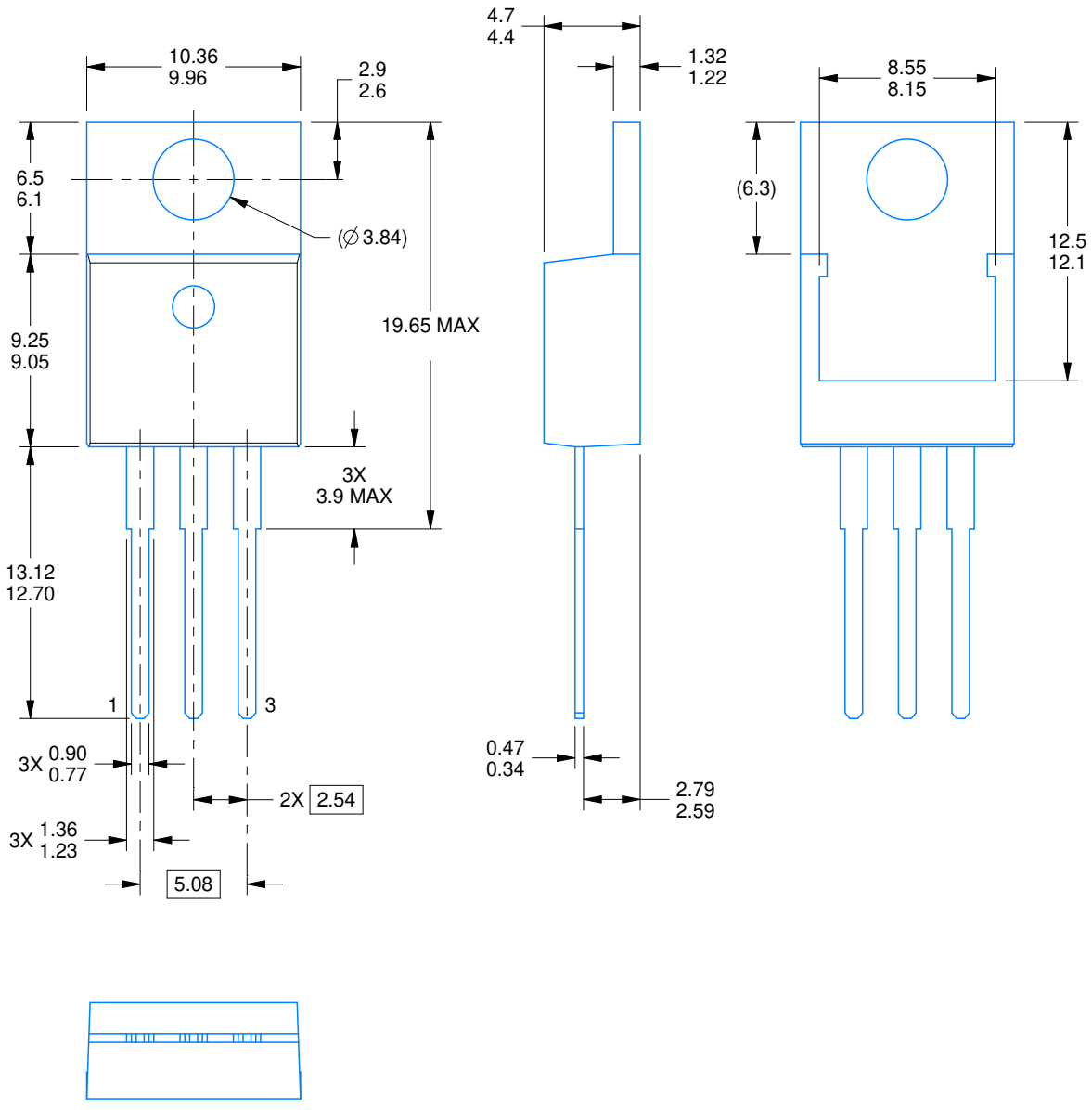


PACKAGE OUTLINE

KCS0003B

TO-220 - 19.65 mm max height

TO-220



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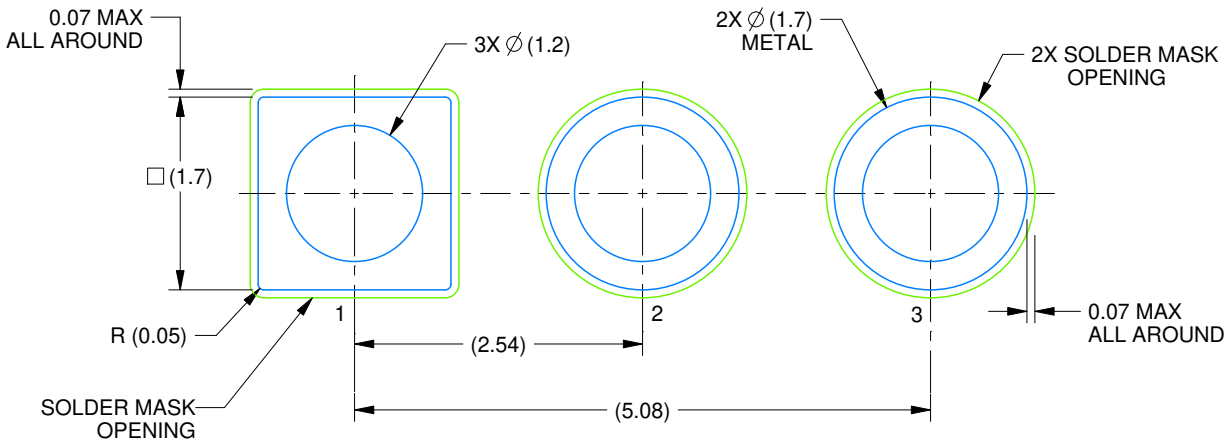
NOTES:

1. Dimensions are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC registration TO-220.



LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE:15X

4222214/B 08/2018

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